

ABSTRACT

Disclosed is a method for the production of a semiconductor component provided with at least one first vertical power component (5,9) and at least one lateral, active component (6) and/or at least one second vertical power component (10) between which is placed at least one trench (2) filled with an insulation (4). Also disclosed is a semiconductor component produced with the method.

The semiconductor component is distinguished by an eccentric or concentric arrangement of the respective functional components (5,6,9,10) which are separated from each other by a trench insulation.

To produce such a semiconductor component, at least one trench (2), which completely encompasses at least one part area of the front side and then is filled with an insulation (4) is etched into a silicon substrate (1). In the further course of the method, the entire area of the silicon substrate (1) is thinned (1) from said back side to said insulation (4), i.e. to the bottom side of the insulation. Contacting of the power components (5,9,10) occurs from the back side.